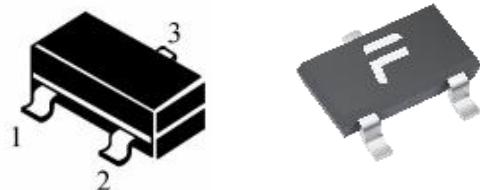
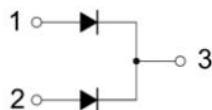


## SOT-23 Switching Diode 开关二极管

### ■ Internal Configuration 内部结构



### ■ Features 特点

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位
Power dissipation 耗散功率	PD(Ta=25°C)	225	mW
Forward Current 正向电流	I <sub>F</sub>	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms 不重复峰值正向浪涌电流	I <sub>FSM</sub>	2000	mA
Reverse Voltage 反向电压	V <sub>R</sub>	50	V
Thermal Resistance J-A 结到环境热阻	R <sub>θJA</sub>	555	°C/W
Junction and Storage Temperature 结温和储藏温度	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

### ■ Device Marking 产品打标

BAV74=JA

### ■ Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压(IR=5uA)	V(BR)	50	—	V
Reverse Leakage Current 反向漏电流(VR=50V)	I <sub>R</sub>	—	0.1	μA
Forward Voltage 正向电压(I <sub>F</sub> =100mA)	V <sub>F</sub>	—	1.0	V
Diode Capacitance 二极管电容(V <sub>R</sub> =0V, f=1MHz)	C <sub>D</sub>	—	2	pF
Reverse Recovery Time 反向恢复时间	T <sub>rr</sub>	—	4	nS

## ■Typical Characteristic Curve 典型特性曲线

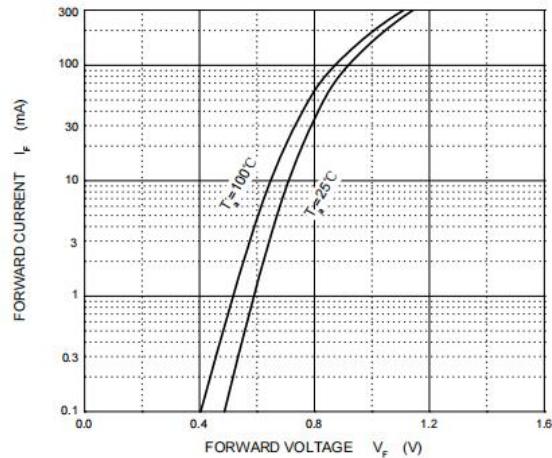


Figure 1: Forward Characteristics

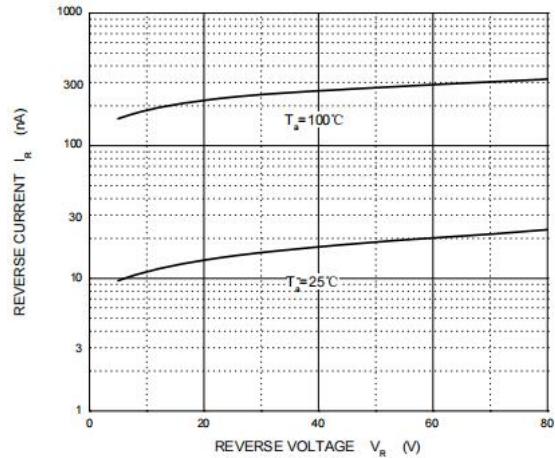


Figure 2: Leakage Current

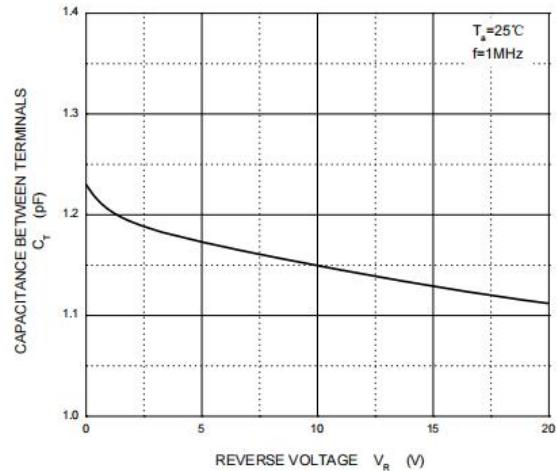


Figure 3: Capacitance Characteristics

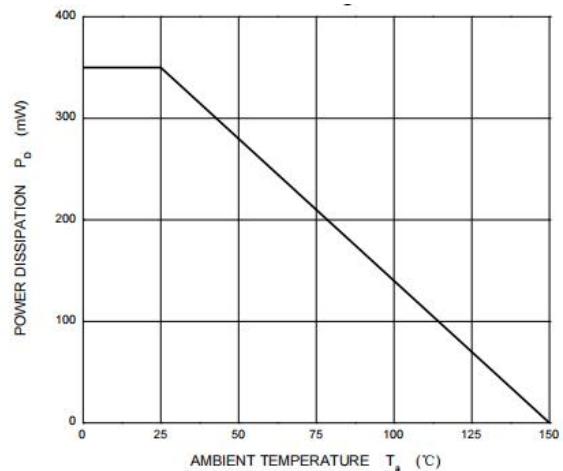
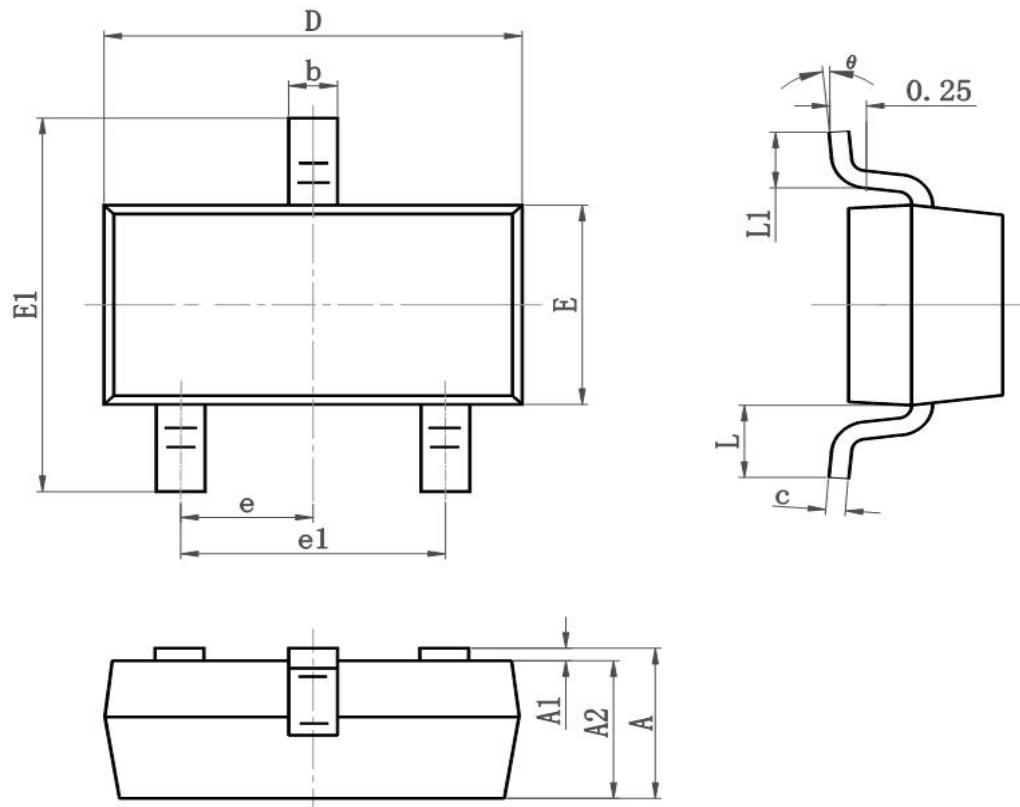


Figure 4: Power Derating Curve

■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°